

Attorney Docket No. 200311972-1; Ser. No. 10/801,341

This listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (Canceled)
2. (Canceled)
3. (Currently amended) The method of claim 2 55, wherein said at least a portion removed comprises material that is substantially unmodified in its material properties.
4. (Currently amended) The method of claim 4 55, wherein the layer of material is formed by use of one or more deposition processes.
5. (Currently amended) The method of claim 4, wherein said deposition processes comprise at least one or more of: spin coating, spraying, dipping, vacuum deposition, and spreading, or combinations thereof.
6. (Canceled)
7. (Currently amended) The method of claim 4 55, wherein said selective modifying further comprises:
performing one or more laser annealing processes on said at least one portion of the formed material layer.
8. (Original) The method of claim 7, wherein at least one of said laser annealing processes comprises localized annealing using a pulsed excimer laser.
9. (Previously presented) The method of claim 7, wherein the formed material layer is selectively annealed, the selection being based at least in part on its position on said substrate.

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10. (Currently amended) The method of claim 4 55, wherein said material properties comprise at least one or more of: conductivity, consolidation, and or crystallinity.

11. (Canceled)

12. (Currently amended) The method of claim 14 56, and further comprising a step for removing at least a substantially unmodified portion of the formed layer of material.

13. (Currently amended) The method of claim 14 56, wherein the layer of material is formed by use of one or more deposition processes.

14. (Currently amended) The method of claim 13, wherein said one or more deposition processes comprise at least one or more of: spin coating, spraying, dipping, vacuum deposition, and spreading, or combinations thereof.

15. (Canceled)

16. (Currently amended) The method of claim 14 56, wherein said step for selectively modifying further comprises:

a step for performing one or more laser annealing processes on said at least one portion of the formed material layer.

17. (Original) The method of claim 16, wherein at least one of said laser annealing processes comprises localized annealing with a pulsed excimer laser.

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18. (Currently amended) The method of claim 16, wherein the formed material layer is selectively annealed based at least in part on its position on said substrate.

19. (Currently amended) The method of claim ~~44~~ 56, wherein said material properties comprise at least one of: conductivity, consolidation, and crystallinity.

20. (Currently amended) The method of claim ~~44~~ 56, wherein said thin film comprises one or more thin films.

21 - 23. (Canceled)

24. (Currently amended) The transparent thin film electronic device of claim ~~23~~ 57, wherein said removing at least a second portion comprises removing material that is substantially unmodified in material properties.

25. (Currently amended) The transparent thin film electronic device of claim ~~23~~ 57, wherein said one or more material layers are formed substantially by a process comprising one or more deposition processes.

26. (Currently amended) The transparent thin film electronic device of claim 25, wherein said one or more deposition processes comprise at least one or more of: spin coating, spraying, dipping, vacuum deposition, and spreading, or combinations thereof.

27. (Canceled)

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28. (Currently amended) The transparent thin film electronic device of claim 23 57, wherein said selective modifying further comprises:

a process substantially comprising one or more laser annealing processes applied to said at least a portion of said one or more material layers.

29. (Previously presented) The transparent thin film electronic device of claim 28, wherein at least one of said one or more laser annealing processes comprises localized annealing using a pulsed excimer laser.

30. (Previously presented) The transparent thin film electronic device of claim 28, wherein said at least a portion of said one or more material layers is selected based at least in part on its position on said substrate.

31. (Currently amended) The transparent thin film electronic device of claim 24 57, wherein said selective modifying comprises selective modification of material properties comprise comprising at least one of: conductivity, consolidation, and crystallinity.

32 - 52. (Canceled)

53. (Currently amended) The method of claim 52 55, wherein the selective modifying of one or more material properties comprises laser annealing of at least the first portion of the formed layer of material.

54. (Currently amended) The method of claim 52 55, wherein the second portion comprises at least a substantially unmodified portion of the formed layer of material.

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55. (New) A method comprising:

a) forming a layer of sol-gel material on at least a portion of at least one surface of a substrate, the layer of sol-gel material being a precursor of a conductive material;

b) selectively modifying one or more material properties of at least a first portion of the formed layer of sol-gel material by selectively directing laser radiation on the first portion; and

c) selectively removing at least a second portion of the formed layer of material.

56. (New) A method of forming a thin film, comprising:

a step for forming a layer of sol-gel material on at least a portion of at least one surface of a substrate, the layer of sol-gel material being a precursor of a conductive material, and

a step for selectively modifying one or more material properties of at least one portion of the formed layer of sol-gel material.

57. (New) A transparent thin film electronic device, formed substantially by a process comprising:

forming one or more material layers on a substrate, at least one of the material layers being a sol-gel precursor of a conductive material;

selectively modifying at least a first portion of the sol-gel precursor of a conductive material; and

removing at least a second portion of the one or more material layers, wherein the at least a second portion comprises one or more non-annealed portions of said one or more material layers.